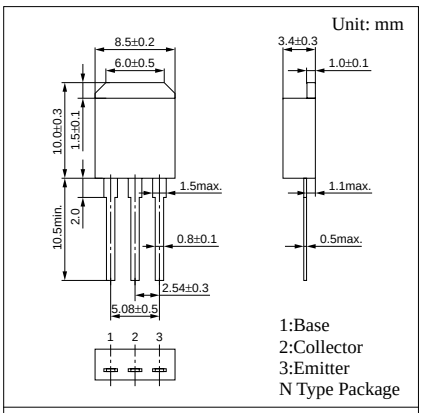
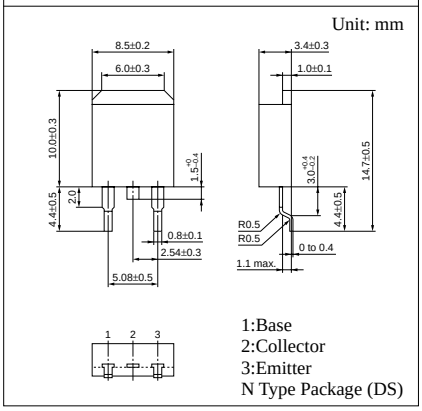
2SD1253, 2SD1253A

Silicon NPN triple diffusion planar type

For power amplification

Complementary to 2SB930 and 2SB930A





Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings (T_C=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage	2SD1253	V_{CBO}	60	V
	2SD1253A		80	
Collector to emitter voltage	2SD1253	V_{CEO}	60	V
	2SD1253A		80	
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	8	A
Collector current		I_C	4	A
Collector power dissipation	T_C=25°C	P_C	40	W
	Ta=25°C		1.3	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

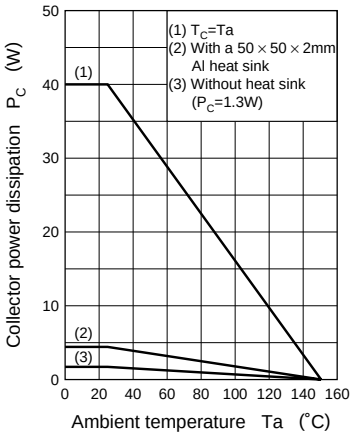
Electrical Characteristics (T_C=25˚C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	2SD1253	I_{CES}	V_{CE} = 60V, V_{BE} = 0			400	μA
	2SD1253A		V_{CE} = 80V, V_{BE} = 0			400	
Collector cutoff current	2SD1253	I_{CEO}	V_{CE} = 30V, I_B = 0			700	μA
	2SD1253A		V_{CE} = 60V, I_B = 0			700	
Emitter cutoff current		I_{EBO}	V_{EB} = 5V, I_C = 0			1	mA
Collector to emitter voltage	2SD1253	V_{CEO}	I_C = 30mA, I_B = 0	60			V
	2SD1253A			80			
Forward current transfer ratio		h_{FE1}*	V_{CE} = 4V, I_C = 1A	40		250	
		h_{FE2}	V_{CE} = 4V, I_C = 3A	15			
Base to emitter voltage		V_{BE}	V_{CE} = 4V, I_C = 3A			2	V
Collector to emitter saturation voltage		$V_{CE(sat)}$	I_C = 4A, I_B = 0.4A			1.5	V
Transition frequency		f_T	V_{CE} = 5V, I_C = 0.5A, f = 1MHz		20		MHz
Turn-on time		t_{on}	I_C = 4A, I_{B1} = 0.4A, I_{B2} = – 0.4A, V_{CC} = 50V		0.4		μs
Storage time		t_{stg}			1.2		μs
Fall time		t_f			0.5		μs

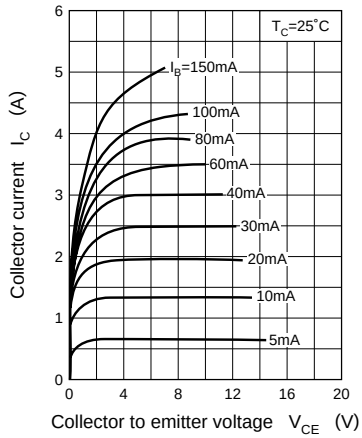
*h_{FE1} Rank classification

Rank	R	Q	P
h_{FE1}	40 to 90	70 to 150	120 to 250

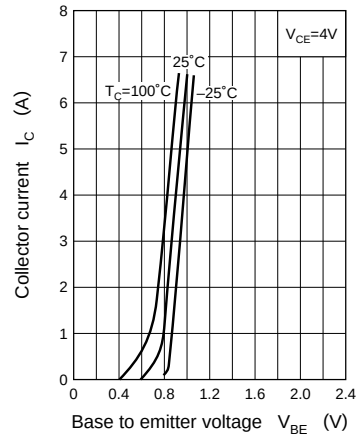
P_C — Ta



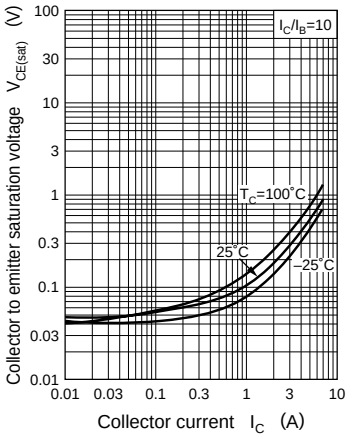
I_C — V_{CE}



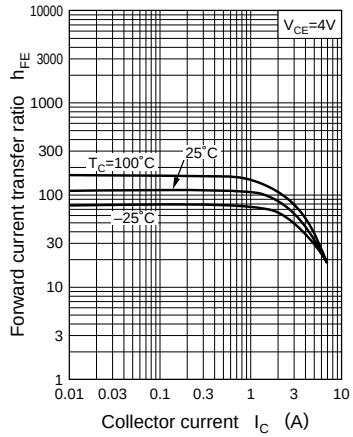
I_C — V_{BE}



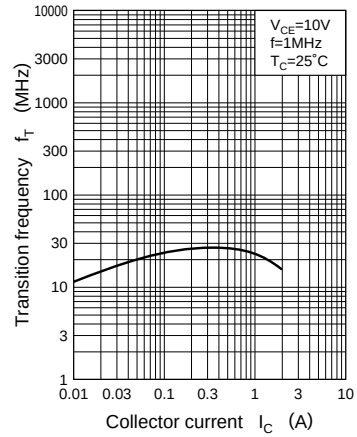
$V_{CE(sat)}$ — I_C



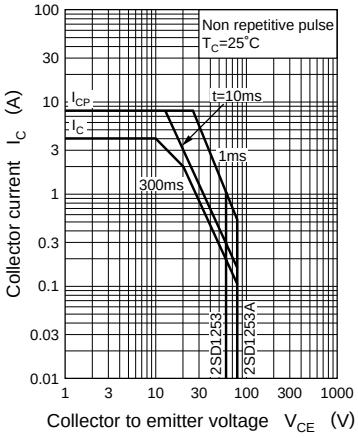
h_{FE} — I_C



f_T — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t